

IPP80N04S403AKSA1

IPP80N04S403AKSA1 Information



For Reference Only

Part Number IPP80N04S403AKSA1

Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 40V 80A TO220-3-1

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IPP80N04S403AKSA1 Specifications

Manufacturer Part Number IPP80N04S403AKSA1 Manufacturer Infineon Technologies Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series OptiMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 40V Current - Continuous Drain (Id) @ 25°C 80A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 53µA Gate Charge (Qg) (Max) @ Vgs 66nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5260pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 44W (Tc) Rds On (Max) @ Id, Vgs 3.7 mOhm @ 80A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3		
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FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)40VCurrent - Continuous Drain (Id) @ 25°C80A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 53μAGate Charge (Qg) (Max) @ Vgs66nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5260pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)94W (Tc)Rds On (Max) @ Id, Vgs3.7 mOhm @ 80A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO220-3-1Package / CaseTO-220-3	Package	TO-220-3
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 80A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 4V @ 53µA Gate Charge (Qg) (Max) @ Vgs 66nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5260pF @ 25V Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.7 mOhm @ 80A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3	Series	OptiMOS?
Drain to Source Voltage (Vdss)40VCurrent - Continuous Drain (Id) @ 25°C80A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 53μAGate Charge (Qg) (Max) @ Vgs66nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5260pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)94W (Tc)Rds On (Max) @ Id, Vgs3.7 mOhm @ 80A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO220-3-1Package / CaseTO-220-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 53μA Gate Charge (Qg) (Max) @ Vgs 66nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5260pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.7 mOhm @ 80A, 10V Operating Temperature 4-55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO220-3-1 Package / Case 70-220-3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 4V @ 53μA Gate Charge (Qg) (Max) @ Vgs 66nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.7 mOhm @ 80A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3	Drain to Source Voltage (Vdss)	40V
Vgs(th) (Max) @ Id 4V @ 53μA Gate Charge (Qg) (Max) @ Vgs 66nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5260pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 94W (Tc) Rds On (Max) @ Id, Vgs 3.7 mOhm @ 80A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3	Current - Continuous Drain (Id) @ 25°C	80A (Tc)
Gate Charge (Qg) (Max) @ Vgs 66nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5260pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 94W (Tc) Rds On (Max) @ Id, Vgs 3.7 mOhm @ 80A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.7 mOhm @ 80A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3	Vgs(th) (Max) @ Id	4V @ 53μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)94W (Tc)Rds On (Max) @ Id, Vgs3.7 mOhm @ 80A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO220-3-1Package / CaseTO-220-3	Gate Charge (Qg) (Max) @ Vgs	66nC @ 10V
FET Feature - Power Dissipation (Max) 94W (Tc) Rds On (Max) @ Id, Vgs 3.7 mOhm @ 80A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3	Input Capacitance (Ciss) (Max) @ Vds	5260pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.7 mOhm @ 80A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs3.7 mOhm @ 80A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO220-3-1Package / CaseTO-220-3	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3	Power Dissipation (Max)	94W (Tc)
Mounting Type Through Hole Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	3.7 mOhm @ 80A, 10V
Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	PG-TO220-3-1
Report errors?	Package / Case	TO-220-3
		Report errors?

IPP80N04S403AKSA1 Guarantees



Ouality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IPP80N04S403AKSA1 Payment Methods



















IPP80N04S403AKSA1 Shipping Methods













If you have any question about IPP80N04S403AKSA1, please do not hesitate to contact us!

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